

WHAT IS CLAIMED IS:

1. A nitride semiconductor laser device chip having a nitride semiconductor stacked-layered structure including an n-type layer, an active layer and a p-type layer successively stacked on a main surface of a nitride semiconductor substrate and having a ridge stripe structure formed in a portion of said p-type layer, wherein
5 said chip has a length L1 of more than 500 μm in a longitudinal direction of said stripe structure and a length L2 of more than 200 μm in a width direction of said stripe structure, and L1/L2 is more than 2.5.
2. The nitride semiconductor laser device chip according to claim 1, wherein a total thickness of said nitride semiconductor substrate and said nitride semiconductor stacked-layered structure is more than 50 μm and less than 200 μm .
3. The nitride semiconductor laser device chip according to claim 1, wherein said stripe structure is formed at a position more than 10 μm away in the width direction of said stripe structure from an edge of said chip.
4. A nitride semiconductor laser apparatus including the nitride semiconductor laser device chip of claim 1 and a support member for placing the nitride semiconductor laser device chip thereon.
5. The nitride semiconductor laser apparatus according to claim 4, wherein said support member has a larger thermal expansion coefficient as compared to said nitride semiconductor substrate.
6. The nitride semiconductor laser apparatus according to claim 4, wherein said support member includes one of Al, Ag, Cu, Au, Fe, Al-SiC, CuW and BeO.
7. The nitride semiconductor laser apparatus according to claim 4,

further including a solder for joining said laser device chip to said support member, and said solder including one of AuSn, AgSn, AuSi, AuGe, PbSn, InSn and AgCuSn.